



### Ultra-Low-Power, Single/Dual-Supply Comparators

### FEATURES

- ◆ Ultra-Low Quiescent Current Over Temperature TSM921/TSM922: 4µA (total) TSM923/TSM924: <2.5µA per comparator</li>
- Single or Dual Power Supplies: Single: +2.5V to +11V Dual: ±1.25V to ±5.5V
- Input Voltage Range Includes Negative Supply
- ♦ 12µs Propagation Delay at 10mV Overdrive
- Push-pull TTL/CMOS-Compatible Outputs
- ♦ Crowbar-Current-Free Switching
- ♦ Continuous Source Current Capability: 40mA
- Internal 1.182V ±1% Reference: TSM921/TSM923/TSM924
- ♦ Adjustable Hysteresis: TSM921/TSM923

### **APPLICATIONS**

Threshold Detectors Window Comparator Level Translators Oscillator Circuits Battery-Powered Systems

### DESCRIPTION

The TSM921–TSM924 family of single/dual/quad, low-voltage, micropower analog comparators is electrically and form-factor identical to the MAX921-MAX924 family of analog comparators. Ideal for 3V or 5V single-supply applications, the TSM921–TSM924 family can operate from single +2.5V to +11V supplies or from ±1.25V to ±5.5V dual supplies. The single TSM921 and the dual TSM922 draw less than 4 $\mu$ A (max) supply current over temperature. The dual TSM923 and the quad TSM924 draw less than 2.5 $\mu$ A per comparator over temperature.

All comparators in this family exhibit an input voltage range from the negative supply rail to within 1.3V of the positive supply. In addition, the comparators' push-pull output stages are TTL/CMOS compatible and capable of sinking and sourcing current. The TSM921/TSM923/TSM924 each incorporates an internal 1.182V ±1% voltage reference. Without complicated feedback configurations and only requiring two additional resistors, adding external hysteresis via a separate pin is available on the single TSM921 and the dual TSM923.

## **TYPICAL APPLICATION CIRCUIT**



A 5V, Low-Parts-Count Window Detector

PART		COMPARATORS PER PACKAGE	
TSM921	Yes	1	Yes
TSM922	No	2	No
TSM923	Yes	2	Yes
TSM924	Yes	4	No

PART	TEMPERATURE RANGE	PACKAGE
TSM921C	0°C to 70°C	8-Pin MSOP/SOIC
TSM921E	-40°C to 85°C	0-FIII WISOF/SOIC
TSM922C	0°C to 70°C	8-Pin MSOP/SOIC
TSM922E	-40°C to 85°C	0-FIII WISOF/SOIC
TSM923C	0°C to 70°C	8-Pin MSOP/SOIC
TSM923E	-40°C to 85°C	
TSM924C	0°C to 70°C	16-Pin SOIC
TSM924E	-40°C to 85°C	10-FIII 30IC



### **ABSOLUTE MAXIMUM RATINGS**

Supply Voltage (V+ to V-, V+ to GND, GND to V-).....-0.3V, +12V

Voltage Inputs	
(IN+, IN-)	(V+ + 0.3V) to (V 0.3V)
HYST	(REF + 5V) to (V 0.3V)
Output Voltage	
REF	(V+ + 0.3V) to (V 0.3V)
OUT (TSM921/24)	(V+ + 0.3V) to (GND - 0.3V)
OUT (TSM922/23)	(V+ + 0.3V) to (V 0.3V)
Input Current (IN+, IN-, HYST)	20mA
Output Current	
REF	
OUT	50mA
Output Short-Circuit Duration (V	+ ≤ 5.5V)Continuous

Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )	
8-Pin MSOP (derate 4.1mW/°C above +70°C)	330mW
8-Pin SOIC (derate 5.88mW/°C above +70°C).	471mW
16-Pin SOIC (8.7mW/°C above +70°C)	696mW
Operating Temperature Range	
TSM92xC	0°C to +70°C
TSM92xE	40°C to +85°C
Storage Temperature Range	
Lead Temperature (soldering, 10s)	+300°C

Electrical and thermal stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to any absolute maximum rating conditions for extended periods may affect device reliability and lifetime.

## **PACKAGE/ORDERING INFORMATION**





## **PACKAGE/ORDERING INFORMATION**

	TOP VIEV	v		TOP VIEW				
OUTA 1								
V- 2	1	7 V+		V- 2		7 V+		
INA+ 3	TSM922			INA+ 3	TSM922	6 INB+		
INA- 4		5 INB-		INA- 4		5 INB-		
	MSOP-8				SO-8			
	UA Packaç	ge			SA Package	9		
ORDER NUMBER	PART MARKING	CARRIER	QUANTITY	ORDER NUMBER	PART MARKING	CARRIER	QUANTITY	
TSM922CUA+		Tube	50	TSM922CSA+	TS922	Tube	97	
1311922007	TABC	Tube	50	TSM922CSA+T	10922	Tape & Reel	2500	
TSM922CUA+T		Таре	2500	TSM922ESA+	TS922E	Tube	97	
1311922004+1	1922CUA+1		2500	TSM922ESA+T	15922E	Tape & Reel	2500	
	TOP VIEW	<u>,</u>		TOP VIEW				
OUTA 1	<b> </b> •	8 OUTB		OUTA 1	<b> </b> •	8 OUTB		
V- 2	TSM923	7 V+		V- [2	7 V+	7 V+		
INA+ 3		6 REF		INA+ 3	6 REF			
INB- 4		5 HYST		INB- 4		5 HYST		
	MSOP-8 UA Packag	e		SO-8 SA Package				
ORDER NUMBER	PART MARKING	CARRIER	QUANTITY	ORDER NUMBER	PART MARKING	CARRIER	QUANTITY	
TSM923CUA+		Tube	50	TSM923CSA+	TS923	Tube	97	
	ТАВА			TSM923CSA+T	10320	Tape & Reel	2500	
TSM923CUA+T		Tape & Reel	2500	TSM923ESA+	TS923E	Tube	97	
			2000	TSM923ESA+T	100202	Tape & Reel	2500	



## **PACKAGE/ORDERING INFORMATION**



Lead-free Program: Silicon Labs supplies only lead-free packaging.

Consult Silicon Labs for products specified with wider operating temperature ranges.



### **ELECTRICAL CHARACTERISTICS – 5V OPERATION**

V+ = 5V, V- = GND = 0V;  $T_A$  = -40°C to +85°C, unless otherwise noted. Typical values are at  $T_A$  = +25°C. See Note 1.

PARAMETER	CONDITIONS				MIN	TYP	MAX	UNITS	
POWER REQUIREMENTS	•						-		
Supply Voltage Range	See Note 2	See Note 2					11	V	
		TSM92	1;	$T_A = +25^{\circ}C$		2.5	3.2		
		HYST =	HYST = REF	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			4		
		TSM922	<u>^</u>	$T_A = +25^{\circ}C$		2.5	3.2		
Supply Current	IN+ = IN- + 100mV	1 3101927	1 3101922	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			4		
Supply Current	10+ = 10- + 100110	TSM92	-	T <sub>A</sub> = +25°C		3.1	4.5	μA	
		HYST =	= REF	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			6		
		TSM924	4	$T_A = +25^{\circ}C$		5.5	6.5		
		1 2101924	4	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			8.5		
COMPARATOR									
Input Offset Voltage	$V_{CM} = 2.5V$						±10	mV	
Input Leakage Current (IN-, IN+)	IN+ = IN- = 2.5V	Т	<sub>A</sub> = -40	°C to +85°C		±0.01	±5	nA	
Input Leakage Current (HYST)	TSM921, TSM923					±0.02		nA	
Input Common-Mode Voltage Range					V-		V+-1.3V	V	
Common-Mode Rejection Ratio	V- to (V+ – 1.3V)	V- to (V+ – 1.3V)				0.1	1	mV/V	
Power-Supply Rejection Ratio	V+ = 2.5V to 11V	$V_{+} = 2.5V \text{ to } 11V$				0.1	1	mV/V	
Voltage Noise	100Hz to 100kHz					20		$\mu V_{RMS}$	
Hysteresis Input Voltage Range	TSM921, TSM923				REF- 0.05V		REF	V	
Response Time	T <sub>A</sub> = +25°C; 100pF I		Overdrive = 10 mV			12			
	$T_A = +25$ C, 100pr I	Cau C	Overdrive = 100 mV			4		μs	
Output High Voltage	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$	: I <sub>OUT</sub> = 1	7mA		V+-0.4			V	
Output Low Voltage	TSM922, TSM923	$T_{A} = -40$	)°C to +	-85°C: I <sub>OUT</sub> = 1.8mA			V-+0.4	V	
Output Low Voltage	TSM921, TSM924	$T_{A} = -40$	)°C to +	-85°C: I <sub>OUT</sub> = 1.8mA			GND + 0.4	V	
REFERENCE									
Reference Voltage	$T_A = 0^{\circ}C$ to +70°C				1.170	1.182	1.194	V	
Reference voltage	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			1.158		1.206	V	
Source Current			T <sub>A</sub> = +25°C		15	25		μA	
Source Current		$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$		6					
Sink Current			$T_A = +$	+25°C	8	15			
	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			40°C to +85°C	4			μA	
Voltage Noise	100Hz to 100kHz	Α				100		μV <sub>RMS</sub>	



### ELECTRICAL CHARACTERISTICS – 3V OPERATION

V+ = 3V, V- = GND = 0V;  $T_A$  = -40°C to +85°C, unless otherwise noted. Typical values are at  $T_A$  = +25°C. See Note 1.

PARAMETER	CONDITIONS			MIN	TYP	MAX	UNITS	
POWER REQUIREMENTS				-				
		TSM921;	T <sub>A</sub> = +25°C		2.4	3.0	μA	
		HYST = REF	$F T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			3.8		
		TSM922	T <sub>A</sub> = +25°C		2.4	3.0		
Supply Current	IN+ = IN- + 100mV		$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			3.8		
Supply Current	110+=110-+1001110	TSM923	T <sub>A</sub> = +25°C		3.4	4.3		
		HYST = REF	F $T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			6		
		TSM924	$T_{A} = +25^{\circ}C$		5.2	6.2		
		13101924	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$			8.0		
COMPARATOR								
Input Offset Voltage	$V_{CM} = 1.5V$					±10	mV	
Input Leakage Current (IN-, IN+)	IN+ = IN- = 1.5V	$T_A =$	40°C to +85°C		±0.01	±5	nA	
Input Leakage Current (HYST)	TSM921, TSM923				±0.02		nA	
Input Common-Mode Voltage Range						V+ – 1.3V	V	
Common-Mode Rejection Ratio	V- to (V+ – 1.3V)		0.2	1	mV/V			
Power-Supply Rejection Ratio	V+ = 2.5V to 11V				0.1	1	mV/V	
Voltage Noise	100Hz to 100kHz	100Hz to 100kHz			20		$\mu V_{RMS}$	
Hysteresis Input Voltage Range	TSM921, TSM923			REF- 0.05V		REF	V	
Response Time	$T_A = +25^{\circ}C; 100 \text{pF load}$ Overdrive = 10 mV Overdrive = 10 mV				14		μs	
Response Time					5			
Output High Voltage	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$	: I <sub>OUT</sub> = 10m/	A Contraction of the second seco	V+-0.4			V	
Output Low Voltage	TSM922, TSM923 $T_A = -40^{\circ}C$ to $+85^{\circ}C$ : $I_{OUT} = 0.8$ mA					V-+0.4	V	
Output Low Voltage	TSM921, TSM924			GND + 0.4	V			
REFERENCE								
Reference Voltage	$T_A = 0^{\circ}C \text{ to } +70^{\circ}C$			1.170	1.182	1.194	V	
Reference voltage	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$	$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$				1.206	V	
Source Current			= +25°C	15	25			
		T <sub>A</sub>	= -40°C to +85°C	6			μA	
Sink Current		T <sub>A</sub>	= +25°C	8	15			
		$T_{A} = -40^{\circ}C \text{ to } +85^{\circ}C$					μA	
Voltage Noise	100Hz to 100kHz				100		$\mu V_{RMS}$	

**Note 1:** All specifications are 100% tested at T<sub>A</sub> = +25°C. Specification limits over temperature (T<sub>A</sub> = T<sub>MIN</sub> to T<sub>MAX</sub>) are guaranteed by device characterization, not production tested.

Note 2: The TSM924 comparator operates below 2.5V. Refer to the "Low-Voltage Operation: V+ = 1.5V (TSM924 Only)" section.



**Output Voltage Low** 

vs Load Current



**Output Voltage High vs** Load Current 5 V+ = 5V 4.5 4 3.5 V<sub>он</sub> - V 3 2.5 V + = 3V2 1.5 10 20 30 40 50 0 LOAD CURRENT - mA

**Reference Voltage vs Temperature** 









# TSM921-TSM924



### **TYPICAL PERFORMANCE CHARACTERISTICS**

 $V_{+} = 5V$ ;  $V_{-} = GND$ ;  $T_{A} = +25^{\circ}C$ , unless otherwise noted.





LOAD CAPACITANCE - nF

Page 8

IN+ INPUT VOLTAGE - mV



**TSM921-TSM924** 

### **TYPICAL PERFORMANCE CHARACTERISTICS**

 $V_{+} = 5V$ ;  $V_{-} = GND$ ;  $T_{A} = +25^{\circ}C$ , unless otherwise noted.







# **PIN FUNCTIONS**

	PIN		NAME	FUNCTION
TSM921	TSM922	TSM923		FUNCTION
1			GND	Ground. Connect to V- for single-supply operation. Output swings from V+ to GND.
_	1	1	OUTA	Comparator A Output. Sinks and sources current. Swings from V+ to V
2	2	2	V-	Negative Supply Voltage. Connect to ground for single-supply operation.
3		_	IN+	Comparator Noninverting Input
—	3	3	INA+	Comparator A Noninverting Input
4	_	_	IN- Comparator Inverting Input	
—	4		INA-	Comparator A Inverting Input
—	5	4	INB-	Comparator B Inverting Input
5	_	5	HYST	Hysteresis Input. Connect to REF if not used. Input voltage range is from $V_{REF}$ to ( $V_{REF}$ - 50mV).
6	_	6	REF	1.182V Reference Output with respect to V
	6		INB+	Comparator B Noninverting Input
7	7	7	V+	Positive Supply Voltage
8	_	_	OUT	Comparator Output. Sinks and sources current. Swings from V+ to GND.
	8	8	OUTB	Comparator B Output. Sinks and sources current. Swings from V+ to V

PIN	NAME	FUNCTION	
<b>TSM924</b>	INAIVIE	FUNCTION	
1	OUTB	OUTB Comparator B Output. Sinks and sources current. Swings from V+ to GND.	
2	OUTA	Comparator A Output. Sinks and sources current. Swings from V+ to GND.	
3	V+	Positive Supply Voltage	
4	INA-	Comparator A Inverting Input	
5	INA+	Comparator A Noninverting Input	
6	INB-	Comparator B Inverting Input	
7	INB+ Comparator B Noninverting Input		
8	REF 1.182V Reference Output with respect to V		
9	V-	Negative Supply Voltage. Connect to ground for single- supply operation.	
10	INC-	Comparator C Inverting Input	
11	INC+	Comparator C Noninverting Input	
12	IND-	Comparator D Inverting Input	
13	IND+	Comparator D Noninverting Input	
14	GND	Ground. Connect to V- for single-supply operation.	
15	OUTD	Comparator D Output. Sinks and sources current. Swings from V+ to GND.	
16	OUTC	Comparator C Output. Sinks and sources current. Swings from V+ to GND.	



# **BLOCK DIAGRAMS**











## THEORY OF OPERATION

The TSM921-TSM924 family of single/dual/quad, low-voltage, micropower analog comparators provide excellent flexibility and performance while sourcing continuously up to 40mA of current. The TSM921, TSM923, and the TSM924 provide an on-board 1.182V ±1% reference voltage. To minimize glitches that can occur with parasitic feedback or due to less than optimal board layout, the design of the TSM921-TSM924 output stage is optimized to eliminate crowbar glitches as the output switches. To minimize current consumption while providing flexibility, the TSM921 and the TSM923 have an on-board HYST pin in order to add additional hysteresis.

### Power-Supply and Input Signal Ranges

The TSM921-TSM924 can operate from a single supply voltage range of +2.5V to +11V, provide a wide common mode input voltage range of V- to V+-1.3V, and accept input signals ranging from V- to V+ - 1V. The inputs can accept an input as much as 300mV above and below the power supply rails without damage to the part. While the TSM921 and the TSM924 are able to operate from a single supply voltage range, a GND pin is available that allows for a dual supply operation with a range of ±1.25V to ±5.5V. If a single supply operation is desired, the GND pin needs to be tied to V-. In a dual supply mode, the TSM921 and the TSM924 are TTL/CMOS compatible with a ±5V voltage and the TSM922 and the TSM923 are TTL compatible with a single +5V supply.

### Low-Voltage Operation: V+ = 1.5V (TSM924 Only)

Due to a decrease in propagation delay and a reduction in output drive, the TSM921-TSM923 cannot be used with a supply voltage much lower than 2.5V. However, the TSM924 can operate down to a supply voltage of 2V; however, as the supply voltage reduces, the TSM924 supply current drops and the performance is degraded. When the supply voltage drops to 2.2V, the reference voltage will no longer function; however, the comparators will function down to a 1.5V supply voltage. Furthermore, the input voltage range is extended to just below 1.5V the positive supply rail. For applications with a sub-2.5V power supply, it is recommended to evaluate the circuit over the entire power supply range and temperature.

#### Comparator Output

The TSM921 and the TSM924 have a GND pin that allows the output to swing from V+ to GND while the V- pin can be set to a voltage below GND as long as the voltage difference between V+ and V- is within 11V. Having a different voltage on V- will not affect the output swing. For TTL applications, V+ can be set to +5V±10% and V- can be set anywhere between 0V and -5V±10%. On the other hand, the TSM922 and the TSM923 do not have a GND pin; hence, for TTL applications, V+ needs to be set to a +5V power supply and V- to 0V. Furthermore, the output design of the TSM921-TSM924 can source and sink more than 40mA and 5mA, respectively, while simultaneously maintaining a quiescent current in the microampere range. If the power dissipation of the package is maintained within the max limit, the output can source pulses of 100mA of current with V+ set to +5V. In an effort to minimize external component count needed to address power supply feedback, the TSM921-TSM924 output does not produce crowbar switching current as the output switches. With a 10mV input overdrive, the propagation delay of the TSM921-TSM924 is 12µs.

### Voltage Reference

The TSM921, TSM923, and TSM924 have an onboard 1.182V reference voltage with an accuracy of  $\pm$ 1%. The REF pin is able to source and sink 15µA and 8µA of current, respectively. The REF pin is referenced to V- and it should not be bypassed.

### Noise Considerations

Noise can play a role in the overall performance of the TSM921-TSM924. Despite having a large gain, if the input voltage is near or equal to the input offset voltage, the output will randomly switch HIGH and LOW. As a result, the TSM921-TSM924 produces a peak-to-peak noise of approximately 0.3mV<sub>PP</sub> while the reference voltage produces a peak-to-peak noise of approximately 1mV<sub>PP</sub>. Furthermore, it is important to design a layout that minimizes capacitive coupling from a given output to the reference pin as crosstalk can add noise and, as a result, degrade performance.



### APPLICATIONS INFORMATION

#### **Hysteresis**

As a result of circuit noise or unintended parasitic feedback, many analog comparators often break into oscillation within their linear region of operation especially when the applied differential input voltage approaches 0V (zero volt). Externally-introduced hysteresis is a well-established technique to stabilizing analog comparator behavior and requires external components. As shown in Figure 1, adding comparator hysteresis creates two trip points: V<sub>THR</sub> (for the rising input voltage) and VTHF (for the falling input voltage). The hysteresis band (V<sub>HB</sub>) is defined as the voltage difference between the two trip points. When a comparator's input voltages are equal, hysteresis effectively forces one comparator input to move quickly past the other input, moving the input out of the region where oscillation occurs. Figure 2 illustrates the case in which an IN- input is a fixed voltage and an IN+ is varied. If the input signals were reversed, the figure would be the same with an inverted output.



Figure 1. Threshold Hysteresis Band

#### Hysteresis (TSM921 and TSM923)

Hysteresis can be generated with two external resistors using positive feedback as shown in Figure 2. Resistor R1 is connected between REF and HYST and R2 is connected between HYST and V-. This will increase the trip point for the rising input voltage, V<sub>THR</sub>, and decrease the trip point for the falling input voltage, V<sub>THF</sub>, by the same amount. If no hysteresis is required, connect the HYST pin to the REF pin. The hysteresis band, V<sub>HB</sub>, is voltage across the REF and HYST pin multiplied by a factor of 2. The HYST pin can accept a voltage between REF



Figure 2. Programming the HYST Pin

and REF-50mV, where a voltage of REF-50mV generates the maximum voltage across R1 and thus, the maximum hysteresis and hysteresis band of 50mV and 100mV, respectively. To design the circuit for a desired hysteresis band, consider the equations below to acquire the values for resistors R1 and R2:

$$R1 = \frac{V_{HB}}{(2 \times I_{REF})}$$
$$R2 = \frac{1.182 - \frac{V_{HB}}{2}}{1 - \frac{1}{2}}$$

 $I_{RFF}$ 

where IREF is the primary source of current out of the reference pin and should be maintained within the maximum current the reference can source. This is typically in the range of 0.1µA and 4µA. It is also important to ensure that the current from reference is much larger than the HYST pin input current. Given  $R2 = 2.4M\Omega$ , the current sourced by the reference is 0.5µA. This allows the hysteresis band and R1 to be approximated as follows:

 $R1(k\Omega) = V_{HB}(mv)$ 

For the TSM923, the hysteresis is the same for both comparators.

#### Hysteresis (TSM922 and TSM924)

Relative to adding hysteresis with the HYST pin as was done for the TSM921 and the TSM923, the circuit in Figure 3 uses positive feedback along with two external resistors to set the desired hysteresis for the TSM924. The circuit consumes more current and it slows down the hysteresis effect due to the





high impedance on the feedback. The following procedure explains the steps to design the circuit for a desired hysteresis:

- 1. Choose R3. As the leakage current at the IN+ pin is less than 1nA, the current through R3 should be at least 100nA to minimize offset voltage errors caused by the input leakage current. For R3 = 11.8M $\Omega$ , the current through R3 is V<sub>REF</sub>/R3 at the trip point. In this case, a 10M $\Omega$  resistor is a good standard value for R3.
- 2. Next, the desired hysteresis band (V\_{HB}) is set. In this example, V\_{HB} is set to 50mV.
- 3. Calculate R1.

$$R1 = R3 \times \frac{V_{HB}}{V_{+}}$$
$$= 10M\Omega \times \frac{50mV}{5V}$$
$$= 100k\Omega$$

In this example, a  $100k\Omega$ , 1% standard value resistor is selected for R1.

- 4. Choose the trip point for  $V_{IN}$  rising  $(V_{THR})$ , which is the threshold voltage at which the comparator switches its output from low to high as  $V_{IN}$  rises above the trip point. In this example, choose  $V_{THR} = 3V$ .
- 5. Calculate R2.

$$R2 = \frac{1}{\left[\left(\frac{V_{THR}}{V_{REF} \times R1}\right) - \frac{1}{R1} - \frac{1}{R3}\right]}$$
$$= \frac{1}{\left[\left(\frac{3}{1.182V \times 100k\Omega}\right) - \frac{1}{100k\Omega} - \frac{1}{10M\Omega}\right]}$$

= 65.44kΩ

In this example, a  $64.9k\Omega$ , 1% standard value resistor is selected for R2.

6. The last step is to verify the trip voltages and hysteresis band using the standard resistance values:

$$V_{THR} = V_{REF} x R1 x \left(\frac{1}{R1} + \frac{1}{R2} + \frac{1}{R3}\right)$$
$$V_{THF} = V_{THR} - \frac{(R1 x V+)}{R3}$$

### **Board Layout and Bypassing**

While power-supply bypass capacitors are not typically required, it is good engineering practice to use  $0.1\mu$ F bypass capacitors close to the device's power supply pins when the power supply impedance is high, the power supply leads are long, or there is excessive noise on the power supply traces. To reduce stray capacitance, it is also good engineering practice to make signal trace lengths as short as possible. Also recommended are a ground plane and surface mount resistors and capacitors.

### **TYPICAL APPLICATION CIRCUITS**

### Auto-Off Power Source

A timed auto power-off circuit can be designed as shown in Figure 4 where the output of the TSM921 is the switched power-supply output. With an internal reference, hysteresis, high current output, and a 2.5  $\mu$ A supply current, the TSM921 provides a wealth of features that make it perfect for this application. While consuming only 3.5 $\mu$ A of quiescent current with a 10mA load, the TSM921 is able to generate a voltage of VBATT – 0.12V. As shown in Figure 4, three resistors are used to generate a hysteresis band of 100mV and sets the IN+ trip point to 50mV when IN+ is going low. The maximum power-on period of the OUT pin before power-down occurs can be determined by the RC time constant as follows:





Figure 4. Auto-Off Power Switch Operates on  $2.5\mu\text{A}$  quiescent current.

#### R x C X 4.6 s

The period value will change depending on the leakage current and the voltage applied to the circuit. For instance:  $2M\Omega \times 10\mu F \times 4.6 \text{ s} = 92 \text{ s}.$ 

#### Window Detector

The schematic shown in Figure 5 is for a 4.5V undervoltage threshold detector and a 5.5V overvoltage threshold detector using the TSM923. Resistor components R1, R2, and R3 can be



#### Figure 5. Window Detector

selected based on the threshold voltage desired while resistors R4 and R5 can be selected based on the hysteresis desired. Adding hysteresis to the circuit will minimize chattering on the output when the input voltage is close to the trip point. OUTA and OUTB generate the active low undervoltage indication and active-low overvoltage indication, respectively. If both OUTA and OUTB signals are ANDed together, the resulting output of the AND gate is an active-high, power-good signal. To design the circuit, the following procedure needs to be followed:

- As described in the section "Hysteresis (TSM921 and TSM923)", determine the desired hysteresis and select resistors R4 and R5 accordingly. This circuit has ±5mV of hysteresis at the input where the input voltage V<sub>IN</sub> will appear larger due to the input resistor divider.
- 2. Selecting R1. As the leakage current at the INB- pin is less than 1nA, the current through R1 should be at least 100nA to minimize offset voltage errors caused by the input leakage current. Values within 100k $\Omega$  and 1M $\Omega$  are recommended. In this example, a 294k $\Omega$ , 1% standard value resistor is selected for R1.
- 3. Calculating R2 + R3. As the input voltage V<sub>IN</sub> rises, the overvoltage threshold should be 5.5V. Choose R2 + R3 as follows:

$$R2 + R3 = R1 \times \left(\frac{V_{OTH}}{V_{REF} + V_{HYS}} - 1\right)$$
$$= 294k\Omega \times \left(\frac{5.5V}{1.182V + 5mV} - 1\right)$$

= 1.068MΩ

 Calculating R2. As the input voltage V<sub>IN</sub> falls, the undervoltage threshold should be 4.5V. Choose R2 as follows:

R2 = (R1 + R2+ R3) x 
$$\frac{(V_{REF}-V_{HYS})}{V_{UTH}}$$
- 294k

$$= (294k\Omega + 1.068M\Omega) \times \frac{(1.182V-5mV)}{4.5} - 294k$$

In this example, a  $61.9k\Omega$ , 1% standard value resistor is selected for R2.

5. Calculating R3.

R3 = (R2 + R3) - R2

- =  $1.068M\Omega 61.9k\Omega$
- = 1.006MΩ



In this example, a  $1M\Omega$ , 1% standard value resistor is selected for R3.

6. Using the equations below, verify all resistor values selected:

$$V_{OTH} = (V_{REF} + V_{HYS}) \times \frac{(R1 + R2 + R3)}{R1}$$

$$V_{OTH} = (V_{REF} - V_{HYS}) \times \frac{(R1 + R2 + R3)}{(R1+R2)}$$

= 4.484V

Where the hysteresis voltage is given by:

$$V_{HYS} = V_{REF} \times \frac{R5}{R4}$$

#### Bar-Graph Level Gauge

A simple four-stage level detector is shown in Figure 6 using the TSM924. Due to its high output source capability, the TSM921 is perfect for driving LEDs. When all of the LEDs are on, the threshold voltage is set by resistors R1 and R2 where  $V_{IN} = (R1 + R2)/R1$  volts. All other threshold voltages are scaled down accordingly by  $\frac{3}{4}$ ,  $\frac{1}{2}$ , and  $\frac{1}{4}$  the threshold voltage. The current through the LEDs is limited by the output resistors.

#### Level Shifter

Figure 7 provides a simple way to shift from bipolar  $\pm 5V$  inputs to TTL signals by using the TSM924. To protect the comparator inputs,  $10k\Omega$  resistors are placed in series and do not have an effect on the performance of the circuit.



Figure 6. Bar-Graph Level Gauge



Figure 7. Level Shifter: ±5V Input into CMOS output



PACKAGE OUTLINE DRAWING





6. Lead span/stand off height/coplanarity are considered as Special characteristic.

# **TSM921-TSM924**



### PACKAGE OUTLINE DRAWING



NOTE:

- 1. PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 2. PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTUSIONS.
- 3. CONTROLLING DIMENSION IN MILIMETERS.
- 4. THIS PART IS COMPLIANT WITH JEDEC MO-187 VARIATIONS AA
- 5. LEAD SPAN/STAND OFF HEIGHT/COPLANARITY ARE CONSIDERED AS SPECIAL CHARACTERISTIC.



### PACKAGE OUTLINE DRAWING



#### NOTE:

- 1. "D" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE.
- "E" DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.25 mm PER SIDE.
- 3. CONTROLLING DIMENSIONS IN MILIMETERS AND ANGLES IN DEGREES.
- 4. THIS PART IS COMPLIANT WITH JEDEC SPECIFICATION MS-012 AB
- 5. LEAD SPAN/STAND OFF HEIGHT/COPLANARITY ARE CONSIDERED AS SPECIAL CHARACTERISTIC.

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